

NV4V31SF

Blue-Violet Laser Diode
405 nm Blue-Violet Laser Light Source

R08DS0070EJ0200 Rev.2.00 Aug 28, 2020

DESCRIPTION

The NV4V31SF is a blue-violet laser diode with a wavelength of 405 nm. A newly developed LD chip structure achieves a high optical power output of 175 mW (CW). The NV4V31SF can provide excellent linearity from low to high output at high temperatures, and reduces the unevenness of beam divergence.

FEATURES

 $\begin{array}{ll} \bullet & \mbox{High optical output power} & P_o = 175 \ mW \ @CW \\ \bullet & \mbox{Peak wavelength} & \lambda_p = 405 \ nm \ TYP. \end{array}$

• Single transverse mode (lateral)

Wide operating temperature range $T_C = -5 \text{ to } +85^{\circ}\text{C}$

• ϕ 5.6 mm CAN package

APPLICATIONS

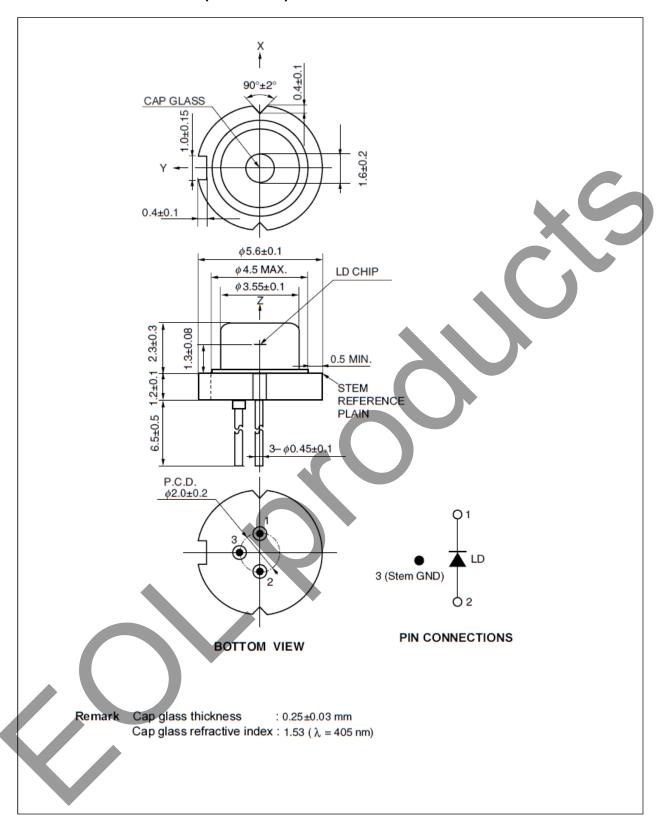
• Blue-violet laser light source





The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

PACKAGE DIMENSIONS (UNIT: mm)



<R> ORDERING INFORMATION

Part Number	Order Number	Rank	Packing Style
NV4V31SF NV4V31SF-A HV		HV	Tray Packing (100 p/Tray), With data
	NV4V31SF-SA-A	XV	Individual Packing (for samples), With data
	NV4V32SF-A	LV	Tray Packing (100 p/Tray), Without data
	NV4V32SF-SA-A	KV	Individual Packing (for samples), Without data

ABSOLUTE MAXIMUM RATINGS (Tc = 25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit	
Optical Output Power (CW)	Po	210	mW	
Reverse Voltage of LD	VR	2	V	
Operating Case Temperature	Tc	−5 to +85	°C	
Storage Temperature	T _{stg}	-40 to +85	°C	

RECOMMENDED OPERATING CONDITIONS ($T_c = 25$ °C, unless otherwise specified)

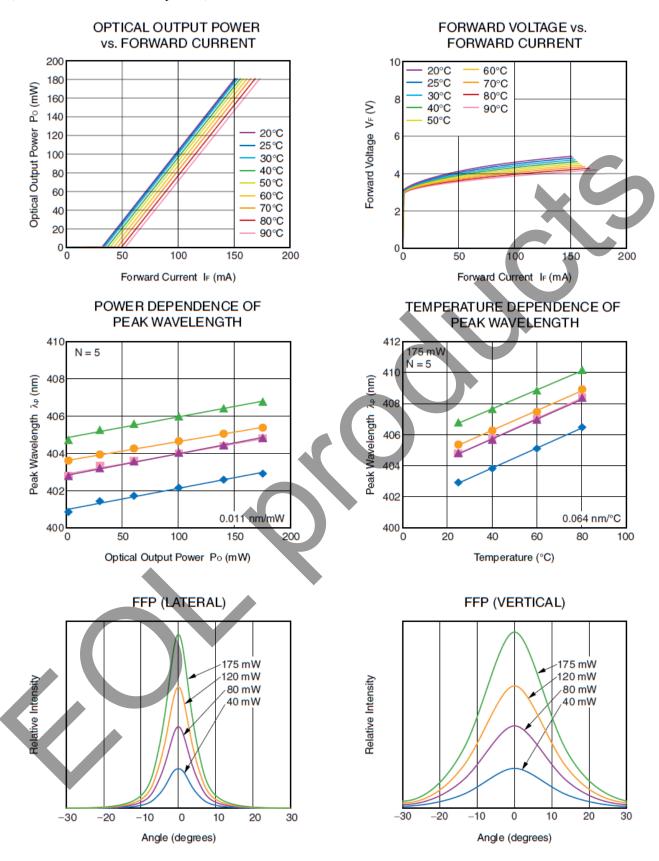
Parameter	Symbol	MAX.	Unit
Optical Output Power (CW)	Po	175	mW

ELECTRO-OPTICAL CHARACTERISTICS (T_C = 25°C, unless otherwise specified)

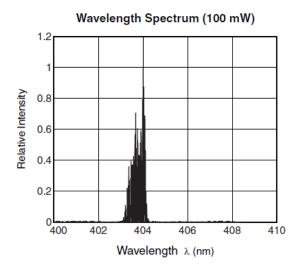
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Threshold Current	I _{th}	CW		35	55	mA
Operating Current	lop	CW, P _o = 175 mW		150	200	mA
Operating Voltage	Vop	CW, P _o = 175 mW		5.0	6.5	V
Slope Efficiency	η_{d}	CW, P _o = 20 mW, 175 mW	1.1	1.55		W/A
Peak Wavelength	λρ	CW, P _o = 175 mW	400	405	410	nm
Beam Divergence (lateral)	<i>O</i> _H	CW, P _o = 175 mW	6	9	12	deg.
Beam Divergence (vertical)	$ heta_{\!\perp}$	$CVV, P_0 = 175 \text{ mVV}$	15	20	25	
Position Accuracy Angle (lateral)	$\Delta \theta_{l/}$	CW D = 175 mW	-3	0	3	deg.
Position Accuracy Angle (vertical)	$arDelta heta_{\!\perp}$	$CW, P_0 = 175 \text{ mW}$	-3	0	3	

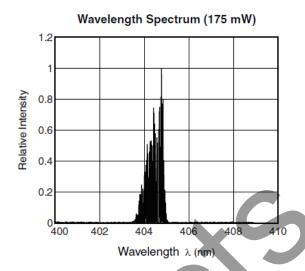
TYPICAL CHARACTERISTICS

 $(T_C = 25^{\circ}C, \text{ unless otherwise specified})$



Remark The graphs indicate nominal characteristics.





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NOTES ON HANDLING

- 1. Recommended soldering conditions
 - Peak Temperature ≤ 350°C
 Time ≤ 3 seconds
 - Soldering of leads should be made at the point 2.0 mm from the root of the lead
 - This device cannot be mounted using reflow soldering.

2. Usage cautions

- (1) Take the following steps to ensure that the device is not damaged by static electricity.
 - Wear an antistatic wrist strap when soldering the device. We recommend a strap with a 1 M Ω resistor.
 - Make sure that the work table and soldering iron are grounded.
 - Make sure that the soldering iron does not leak.
- (2) Do not subject the package to undue stress.

The package has a tensile strength of 1N or less.

Do not exceed this rating. Also, avoid bending the leads as much as possible.

If the leads must be bent, bend them only once, making sure to anchor the stem base of the lead

- (3) Do not allow the cap glass of the package to become scratched or dirty. Also, do not subject the cap glass to external force.
- (4) Be sure to attach a heat sink to sufficiently dissipate heat.
- (5) Use the device as soon as possible after opening the bag.



SAFETY INFORMATION ON THIS PRODUCT



SEMICONDUCTOR LASER



AVOID EXPOSURE-Invisible Laser Radiation is emitted from this aperture

Warning

Laser Beam

A laser beam is emitted from this diode during operation.

If the laser beam or its reflection enters your eye, it may cause injury to the eye or loss of eyesight. (Note that, depending on the wavelength of the beam, the laser beam might not be visible.)

- Do not look directly into the laser beam.
- · Avoid exposure to the laser beam, any reflected or collimated beam.



Revision History

NV4V31SF Data Sheet

		Description		
Rev.	Date	Page	Summary	
0.01	Jan 23, 2013	_	First edition issued	
1.00	Jun 20, 2013	p.2	Modification of PACKAGE DIMENSIONS	
		p.3	Modification of ORDERING INFORMATION	
2.00	Aug 28,2020	p.3	Modification of ORDERING INFORMATION	
			(Newly established NV4V31SF-SA-A, NV4V32SF-SA-A)	
			(Added NV4V32SF-A)	

